Time		Coherence	Qubit	Material	Host	Date	Reference	Source	0
57	s	T_1	LD/e	GaAs/AlGaAs	2D	2018-08	1	p3 and Fig. 4a	1
30	s	T_1	LD/i	Si:P	imp	2017-03	2	Fig. 2b the lowest point	2
11	s[a]	T_1	LD/i	Si:P	imp	2023-02	3	p6	3
10	s	T_1	LD/e	GaAs/AlGaAs	2D	2017-10	4	Fig. 2 the lowest green point	4
9.8	s	T_1	LD/i	Si:P	imp	2019-05	5	Fig. 2c	5
9.3	s	T_1	LD/i	Si:P	imp	2018-03	6	p3 and Fig. 1f	6
9	s	T_1	LD/e	Si/SiO$_2$	1D	2021-03	7	p3 and Fig. 3a the leftmost blue point	7
6.5	s	T_1	LD/i	^{28}Si:P	imp	2023-02	8	Fig. 3c	8
6	s	T_1	LD/i	Si:P	imp	2010-09	9	p2	9
5	s[b]	T_1	LD/e	Si/SiGe	2D	2019-04	10	p4	10
4.2	s	T_1	LD/i	Si:P	imp	2019-01	11	p3	11
3.4	s	T_1	LD/i	^{28}Si:P	imp	2021-01	12	p6 and SFig. 3c	12
3	s	T_1	LD/i	^{28}Si:P	imp	2016-10	13	p3	13
3	s	T_1	ST/e	Si/SiGe	2D	2012-01	14	p4	14
2.8	s	T_1	LD/e	Si/SiGe	2D	2011-04	15	p3 and Fig. 3	15
2.6	s	T_1	LD/e	Si/SiO$_2$	2D	2013-06	16	p3	16
1.8	s	T_1	LD/i	Si:P	imp	2013-06	17	Fig. 3	17
1.6	s	T_1	LD/e	^{28}Si/SiO$_2$	2D	2022-03	18	p4 and Fig. 3c	18
1.3	s	T_1	LD/i[c]	^{28}Si:P	imp	2016-10	19	p4	19
1.3	s	T_1	LD/i	Si:P	imp	2018-11	20	p3 and Fig. 2b	20
1	s	T_1	LD/e	^{28}Si/SiGe	2D	2020-03	21	p6 and Fig. 4a	21
1	s	T_1	LD/e	^{28}Si/SiO$_2$	2D	2018-10	22	p2	22
1	s	T_1	LD/e	GaAs/AlGaAs	2D	2008-01	23	p4 and Fig. 3c the leftmost blue point	23
0.7	s	T_1	LD/i	Si:P	imp	2012-09	24	p3	24
0.6	s[d]	T_1	LD/e	Si/SiGe	2D	2009-08	25	Fig. 5	25
0.5	s[e]	T_1	ST/e	^{28}Si/SiO$_2$	2D	2020-04	26	Fig. 4 the leftmost black point	26
0.17	s	T_1	LD/e	Si/SiGe	2D	2016-11	27	Fig. 6	27
0.16	s[f]	T_1	LD/e	Si/SiGe	2D	2019-04	10	Fig. 2	28
0.15	s[g]	T_1	LD/e	^{28}Si/SiO$_2$	2D	2018-08	28	p2 and p4	29
0.14	s	T_1	ST/e	Si/SiGe	2D	2012-04	29	Fig. 2d	30
0.13	s	T_1	LD/e	^{28}Si/SiGe	2D	2019-11	30	p4	31
90	ms	T_1	LD/e	Si/SiO$_2$	2D	2020-06	31	Fig. 1c	32
85	ms	T_1	LD/e	GaAs/AlGaAs	2D	2014-12	32	p2 and Fig. 3	33
50	ms	T_1	LD/e	Si/SiGe	2D	2018-02	33	p1 and ED Fig. 3b	34
40	ms	T_1	LD/e	Si/SiO$_2$	2D	2010-03	34	p4 and Fig. 4 the leftmost red point	35
34	ms	T_1	ST/e	BLG	2D	2023-04	35	p5 and Fig. 3a	36
32	ms	T_1	LD/h	Ge/SiGe	2D	2020-08	36	p3	37
32	ms	T_1	LD/e	^{28}Si/SiGe	2D	2022-12	37	p3	38
22	ms[h]	T_1	LD/e	Si/SiGe	2D	2022-08	38	p2 and ED Fig. 4b-d	39
20	ms	T_1	HY/e[i]	^{28}Si/SiGe	2D	2022-03	39	p5	40
16	ms	T_1	LD/h	Ge/SiGe	2D	2021-03	40	Fig. S5 dot 3	41
15	ms[j]	T_1	ST/e	^{28}Si/SiO$_2$	2D	2020-04	26	Fig. 4 the rightmost black point	42
10	ms	T_1	LD/e	Si/SiO$_2$	1D	2021-09	41	p2 and Fig. 2a	43
8.4	ms	T_1	LD/h	BLG	2D	2022-05	42	p5 and Fig. 4	44
5	ms	T_1	LD/i	^{28}Si:B	imp	2020-07	43	p3 and Fig. 3b	45
5	ms[k]	T_1	ST/e	^{28}Si/SiO$_2$	2D	2021-01	44	p4 and Fig. 1d	46
4.1	ms	T_1	ST/i	Si:P	imp	2014-06	45		47
3.7	ms	T_1	LD/e	GaAs/AlGaAs	2D	2016-07	46	p3 and Fig. 2	48
3.7	ms	T_1	LD/e[l]	^{28}Si/SiO$_2$	2D	2020-04	47	p2	49
3.1	ms	T_1	LD/i	^{28}Si:P	imp	2022-01	48	ED Fig. 3 first column	50

TABLE I-1. Spin coherence times (part 1). Superscripts stand for the following. [a]: Dot D3. [b]: No micromagnet. [c]: Qubit defined in the rotating frame. [d]: *(estimated)* Fig. 5 the lowest point. [e]: At 0.04 kelvin. [f]: With micromagnet. [g]: At 0.1 kelvin. [h]: The average over the three qubits. [i]: EO qubit. [j]: At 1.5 kelvin. [k]: Lifetime of T_- state. [l]: At 1 kelvin.

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